



SamHop Microelectronics Corp.

STS 3405

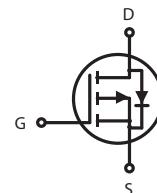
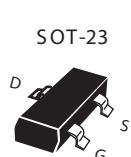
Sep.15 2005

P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-30V	-3A	100 @ V _{GS} = -10V
		130 @ V _{GS} = -4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- SOT-23 Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous @ T _J =25°C -Pulsed ^b	I _D	- 3	A
	I _{DM}	- 12	A
Drain-Source Diode Forward Current	I _S	-1.25	A
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	100	°C/W
--	------------------	-----	------

STS 3405

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$		-1		μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$		± 100		nA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -3A$		75	100	m-ohm
		$V_{GS} = -4.5V, I_D = -2A$		100	130	m-ohm
On-State Drain Current	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	8			A
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -3A$		8		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V$ $f = 1.0MHz$		435		pF
Output Capacitance	C_{oss}			90		pF
Reverse Transfer Capacitance	C_{rss}			60		pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = -15V,$ $I_D = -1A,$ $V_{GEN} = -10V,$ $R_{GEN} = 6\ ohm$		8		ns
Rise Time	t_r			6.8		ns
Turn-Off Delay Time	$t_{D(OFF)}$			37		ns
Fall Time	t_f			13		ns
Total Gate Charge	Q_g	$V_{DS} = -15V, I_D = -3A, V_{GS} = -10V$		7.8		nC
Gate-Source Charge	Q_{gs}	$V_{DS} = -15V, I_D = -3A,$ $V_{GS} = -10V$		0.58		nC
Gate-Drain Charge	Q_{gd}			2.2		nC

STS3405

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = -1.25A$			-0.8	-1.25

Notes

- a. Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.
- b. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- c. Guaranteed by design, not subject to production testing.

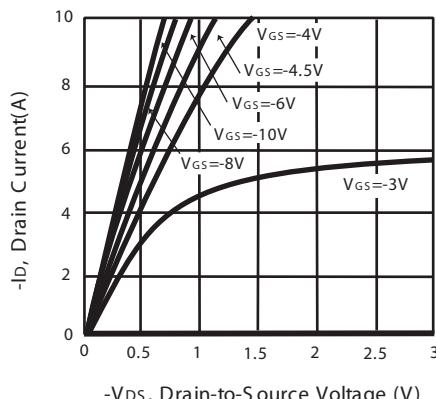


Figure 1. Output Characteristics

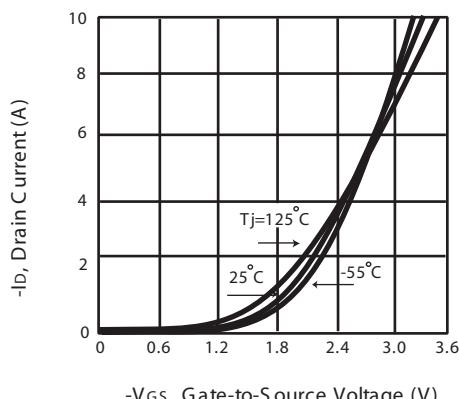


Figure 2. Transfer Characteristics

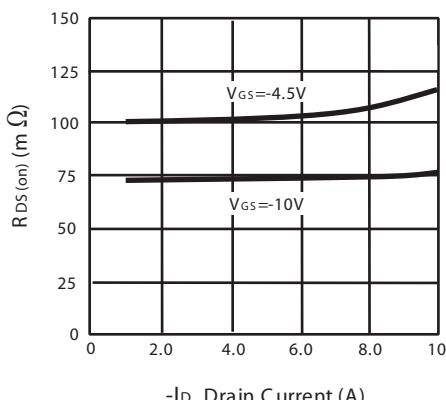


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

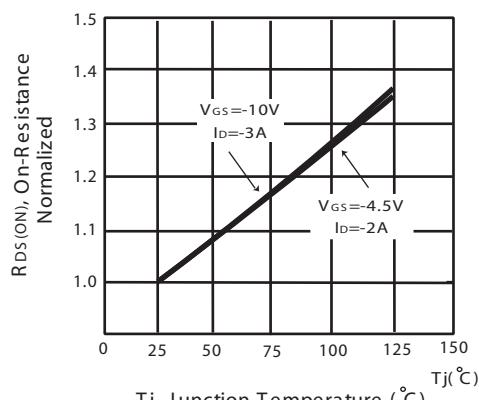


Figure 4. On-Resistance Variation with Drain Current and Temperature

STS3405

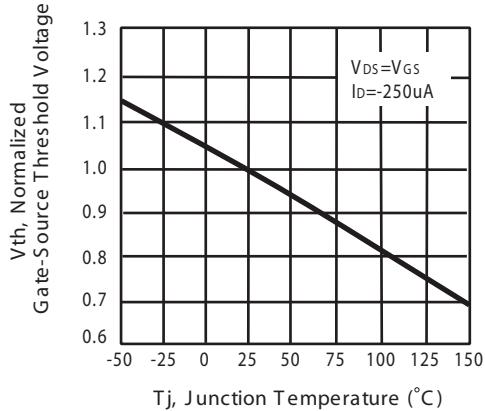


Figure 5. Gate Threshold Variation with Temperature

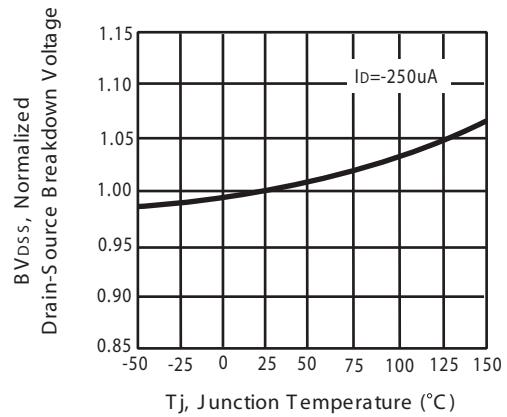


Figure 6. Breakdown Voltage Variation with Temperature

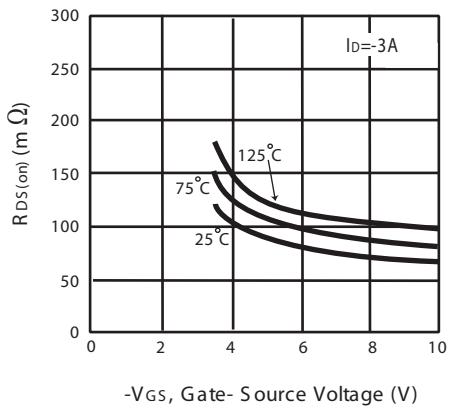


Figure 7. On-Resistance vs. Gate-Source Voltage

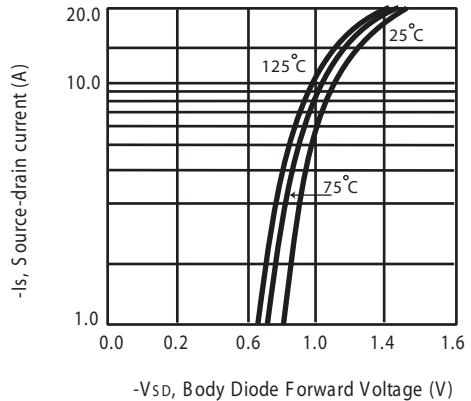


Figure 8. Body Diode Forward Voltage Variation with Source Current

STS 3405

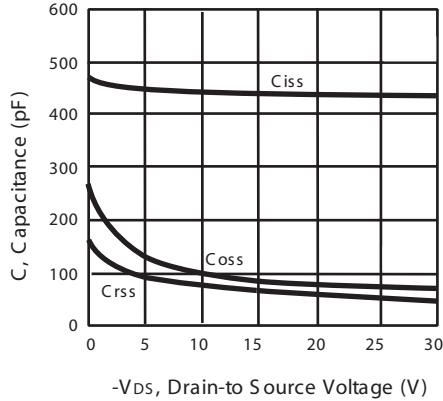


Figure 9. Capacitance

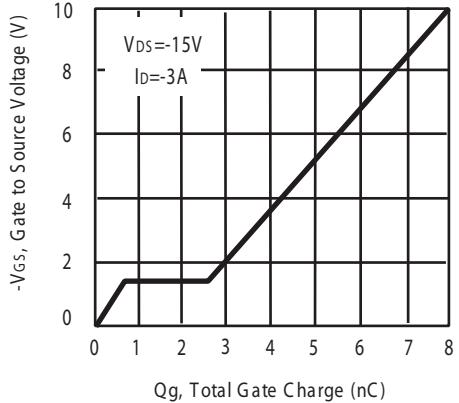


Figure 10. Gate Charge

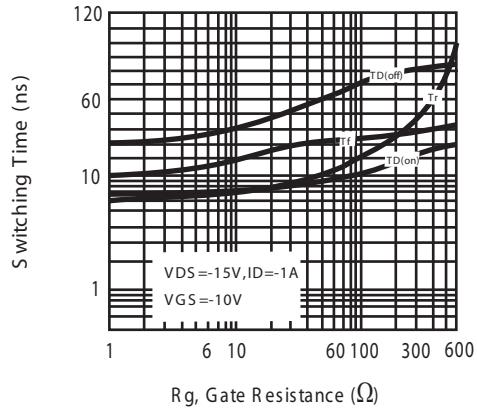


Figure 11. switching characteristics

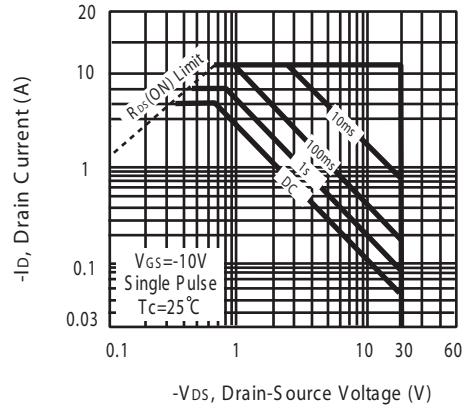


Figure 12. Maximum Safe Operating Area

STS3405

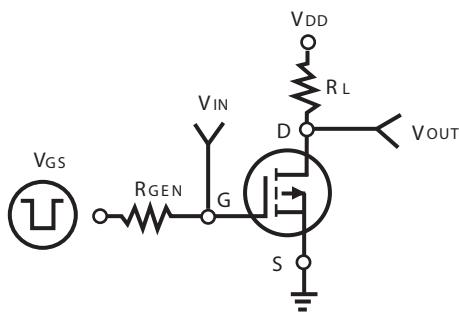


Figure 11. Switching Test Circuit

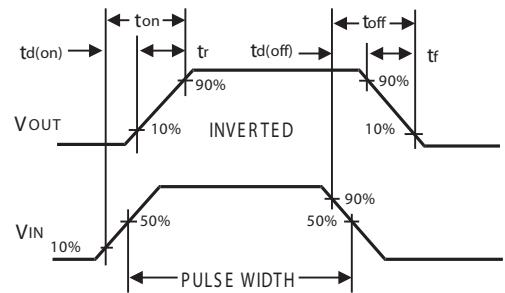
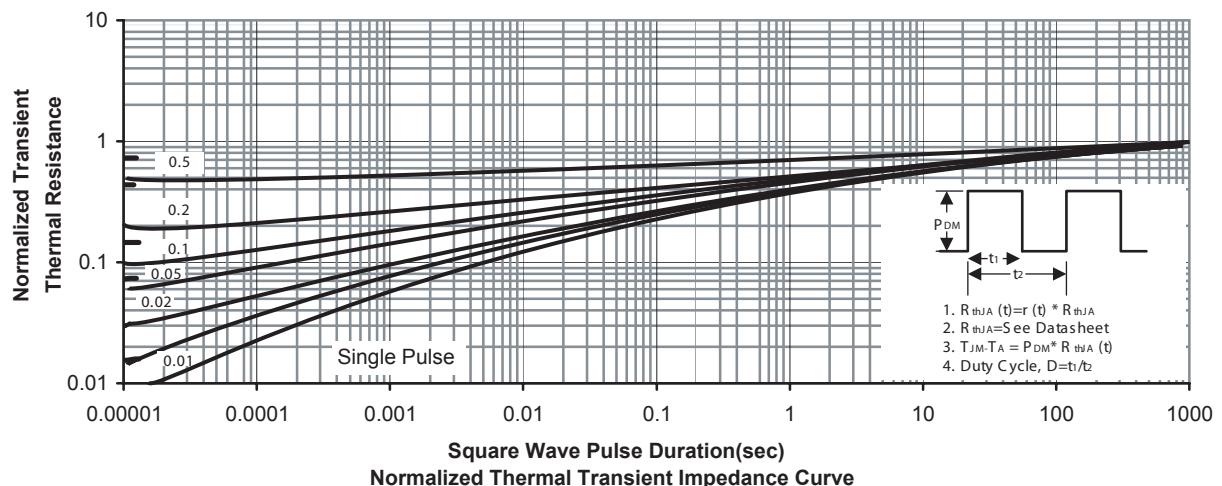


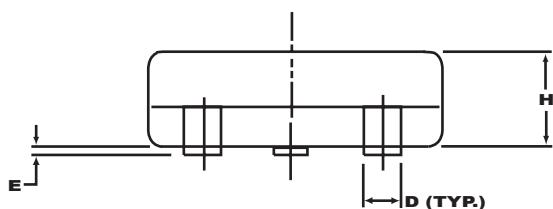
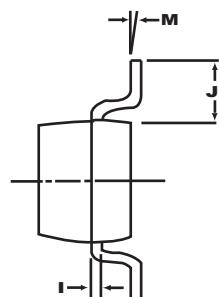
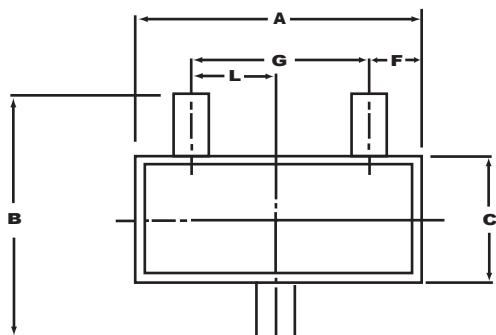
Figure 12. Switching Waveforms



STS 3405

PACKAGE OUTLINE DIMENSIONS

SOT-23

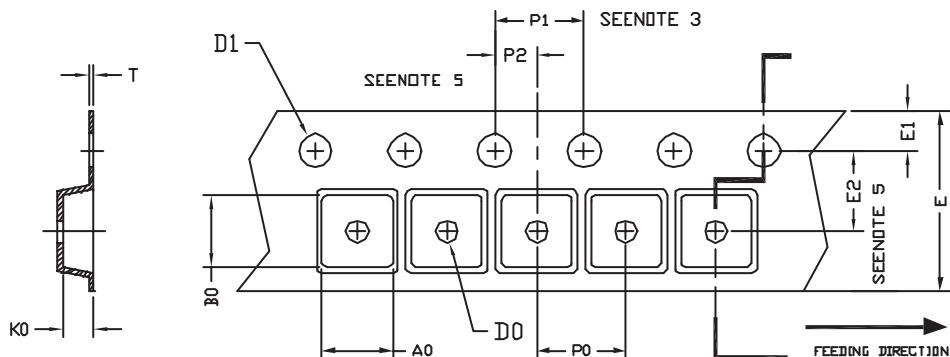


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.10	0.106	0.122
B	2.40	2.80	0.094	0.110
C	1.40	1.60	0.055	0.063
D	0.35	0.50	0.014	0.020
E	0	0.10	0	0.004
F	0.45	0.55	0.018	0.022
G	1.90 REF.		0.075 REF.	
H	1.00	1.30	0.039	0.051
I	0.10	0.20	0.004	0.008
J	0.40	-	0.016	-
L	0.45	1.15	0.033	0.045
M	0°	10°	0°	10°

STS 3405

SOT-23 Tape and Reel Data

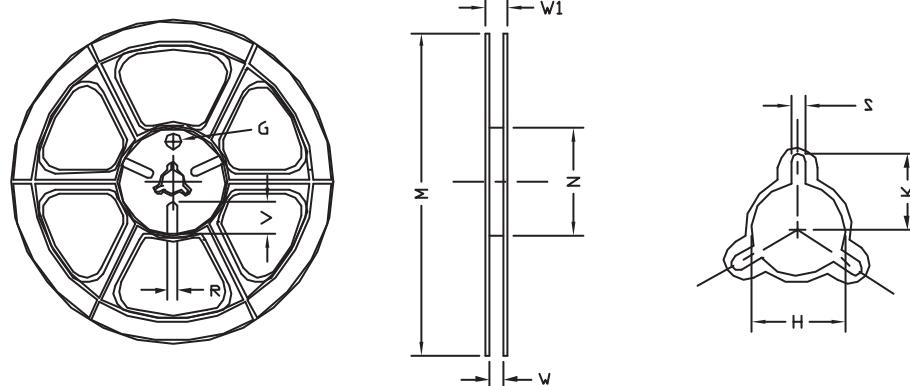
SOT-23 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23	3.20 ±0.10	3.00 ±0.10	1.33 ±0.10	1.00 +0.25	1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.02

SOT-23 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	178	178 ±1	60 ±1	9.00 ±0.5	12.00 ±0.5	13.5 ±0.5	10.5	2.00 ±0.5	10.0	5.00	18.00